

AFN3400S23RG-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUC	CT SUMMARY		
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)
30	0.030 at V _{GS} = 10 V	6.5	4.5 nC
30	0.033 at V _{GS} = 4.5 V	6.0	4.5110

FEATURES

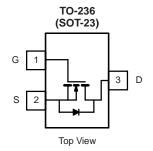
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

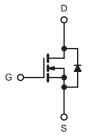


ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

DC/DC Converter





N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	I GS T _A = 25 °C,	unless othe	rwise noted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
	T _C = 25 °C		6.5 ^a		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I _D	6.0		
Continuous Brain Current (1) = 130 C)	T _A = 25 °C		5.3		
	T _A = 70 °C	1	5.0	A	
Pulsed Drain Current	•	I _{DM}	25		
	T _C = 25 °C		1.4		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	0.9 ^{b, c}		
	T _C = 25 °C		1.7		
Maximum Power Dissipation	T _C = 70 °C	T _C = 70 °C P _D	1.1	W	
Maximum Fower Dissipation	T _A = 25 °C] ' ^U [1.1 ^{b, c}	VV	
	$T_A = 70 ^{\circ}C$] [0.7 ^{b, c}		
erating Junction and Storage Temperature Range T _J , T _{stg} - 55 to 150		90			
Soldering Recommendations (Peak Temperature) ^{d, e}			260	°C	

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	90	115	°C/W			
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	60	75] 0/11			

Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 130 °C/W.



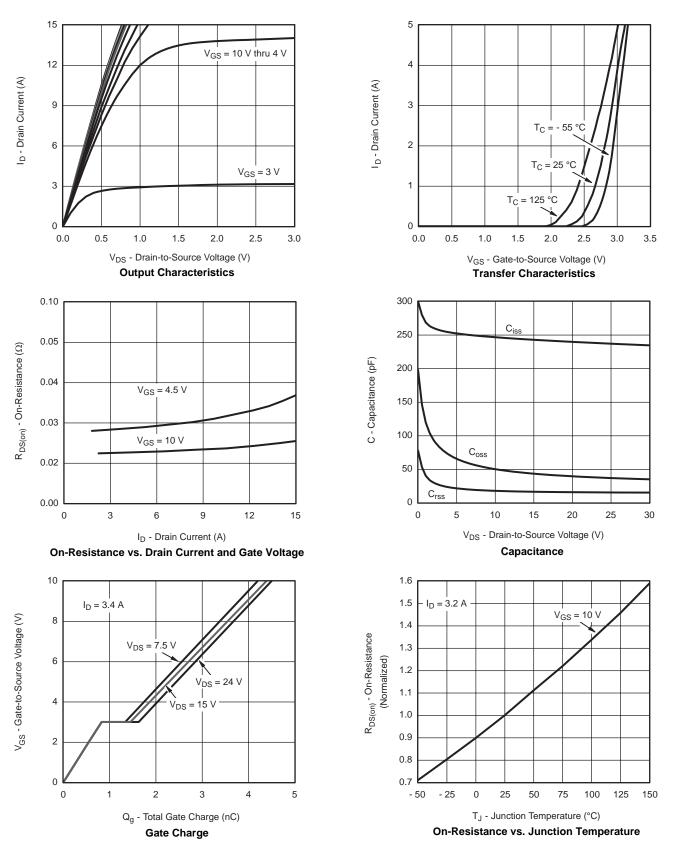
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static					L	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I 250 · · A		31		>1/06
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	$I_D = 250 \mu A$		- 5		mV/°0
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.7	1.1	2.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zana Oata Valtana Bua'a Oamaat		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α
		V _{GS} = 10 V, I _D = 3.2 A		0.030		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$		0.033		Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 4.8 A		11		S
Dynamic ^b				L		
Input Capacitance	C _{iss}			335		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		45		pF
Reverse Transfer Capacitance	C _{rss}			17		
Total Oats Observe		$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3.4 \text{ A}$		4.5	6.7	
Total Gate Charge	Qg			2.1	3.2	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 3.4 \text{ A}$		0.85		
Gate-Drain Charge	Q_{gd}			0.65		
Gate Resistance	R_g	f = 1 MHz	0.8	4.4	8.8	Ω
Turn-On Delay Time	t _{d(on)}			12	20	
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		50	75	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 2.7 A, V_{GEN} = 4.5 V, R_g = 1 Ω		12	20	
Fall Time	t _f			22	35	1
Turn-On Delay Time	t _{d(on)}			5	10	ns -
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		12	20	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 2.7 A, V_{GEN} = 10 V, R_g = 1 Ω		10	15	
Fall Time	t _f			5	10	
Drain-Source Body Diode Characteristic	cs					
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			1.4	Α
Pulse Diode Forward Current	I _{SM}				15	
Body Diode Voltage	V_{SD}	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			10	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 2.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		5	10	nC
Reverse Recovery Fall Time	t _a	1 2.7 A, al/at - 100 A/µs, 1J = 25 C		6		200
Reverse Recovery Rise Time	t _b			4		ns

Notes:

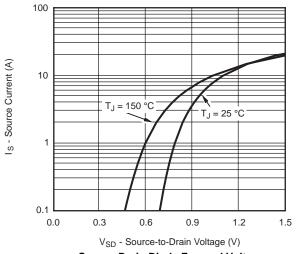
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

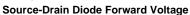
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

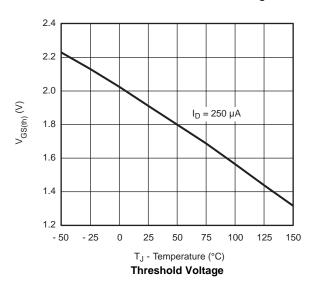


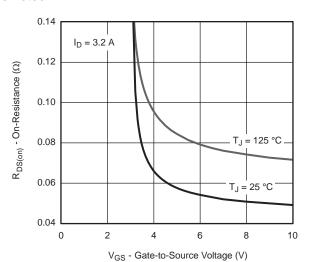




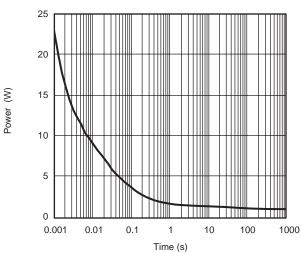




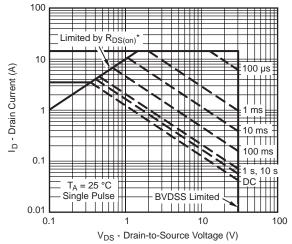




On-Resistance vs. Gate-to-Source Voltage



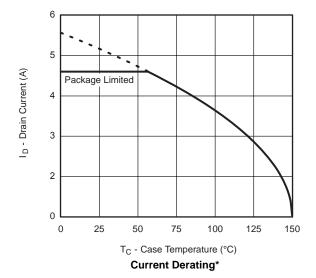
Single Pulse Power

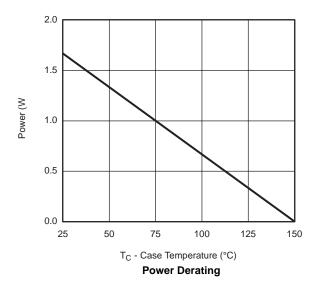


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

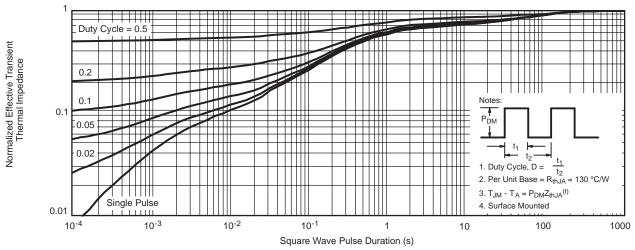






^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





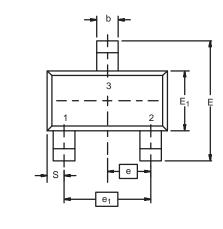
Normalized Thermal Transient Impedance, Junction-to-Ambient

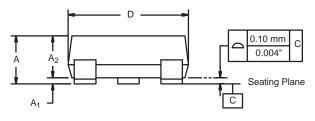


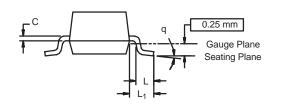
Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







Dim -	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	Ref	
S	0.50 Ref		0.020) Ref	
q	3°	8°	3°	8°	

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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